IN THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming a ~~first leveling~~ passivation film ~~containing a siloxane structure over~~ directly formed on the ~~gate~~ wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first leveling~~ passivation film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

2. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming a ~~first leveling~~ passivation film ~~containing a siloxane structure over~~ covering a surface of the ~~gate~~ wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first leveling~~ passivation film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film,~~ ~~and~~

~~wherein the thickness of the first leveling film is 0.1 μm or more and less than 1.5 μm~~.

3. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming a ~~first leveling~~ passivation film ~~containing a siloxane structure over~~ deposited on the ~~gate~~ wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first leveling~~ passivation film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film,~~ ~~and~~

~~wherein the thickness of the second leveling film is from 0.1 μm to 2.9 μm inclusive~~.

4. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming ~~a first leveling~~ an insulating film ~~containing a siloxane structure over~~ directly formed on the ~~gate~~ wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first leveling~~ insulating film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film, and~~

~~wherein the total thickness of the first leveling film and the second leveling film is from 0.2 μm to 3.0 μm~~.

5. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming ~~a first leveling~~ an insulating film ~~containing a siloxane structure over~~ covering a surface of the ~~gate~~ wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first~~ ~~leveling~~ insulating film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film, and~~

~~wherein the first leveling film and the second leveling film are insulating films formed by spin coating~~.

6. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

~~forming a wiring over the gate wiring;~~

forming ~~a first leveling~~ an insulating film ~~containing a siloxane structure over~~ deposited the wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first leveling~~ insulating film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

7. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming ~~a first leveling~~ an insulating film ~~containing a siloxane structure over~~ directly formed on the ~~gate~~ wiring;

forming a ~~second~~ leveling film containing a siloxane structure on the ~~first leveling~~ insulating film; and

forming a pixel electrode ~~on~~ connecting the wiring through a second hole in the insulating film and the leveling film over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film,~~ ~~and~~

~~wherein the first leveling film and the second leveling film comprise the same material~~.

8. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming ~~a first leveling~~ an insulating film ~~of a resin containing a siloxane structure over~~ directly formed on the ~~gate~~ wiring;

forming a ~~second~~ leveling film ~~of a resin~~ containing a siloxane structure on the ~~first leveling~~ insulating film;

forming a pixel electrode ~~on~~ connecting the wiring through a second hole in the insulating film and the leveling film over the ~~second~~ leveling film; and

forming an ~~EL~~ elecroluminescence layer over the pixel electrode~~,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

9. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming a first insulating film ~~comprising an inorganic material over the gate insulating film~~ directly formed on the wiring;

forming a ~~first~~ leveling film containing a siloxane structure ~~over~~ on the first insulating film;

~~forming a second leveling film containing a siloxane structure on the first leveling film;~~

forming a pixel electrode ~~on~~ connecting the wiring through a second hole in the first insulating film and the leveling film over the ~~second~~ leveling film; and

forming ~~an EL layer~~ a second insulating film over the pixel electrode~~,~~; and

forming an electro luminescence layer over the pixel electrode and the second insulating film

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

10. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

~~applying a first layer containing a siloxane structure by spin coating;~~

~~baking the first layer to form a first leveling film;~~

~~applying a second layer containing a siloxane structure by spin coating;~~

~~baking the second layer to form a second leveling film;~~

forming a passivation film directly formed on the wiring;

forming a leveling film formed by a spin coating method on the passivation film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

11. (canceled)

12. (previously presented) The method according to claim 1, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

13. (canceled)

14. (previously presented) The method according to claim 2, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

15. (canceled)

16. (previously presented) The method according to claim 3, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

17. (canceled)

18. (previously presented) The method according to claim 4, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

19. (canceled)

20. (previously presented) The method according to claim 5, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

21. (canceled)

22. (previously presented) The method according to claim 6, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

23. (canceled)

24. (previously presented) The method according to claim 7, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

25. (canceled)

26. (previously presented) The method according to claim 8, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

27. (canceled)

28. (previously presented) The method according to claim 9, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

29. (canceled)

30. (previously presented) The method according to claim 10, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

31. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming a ~~first inorganic film on~~ passivation film covering a surface of the ~~gate~~ wiring;

~~forming a wiring on the first inorganic film;~~

~~forming a second inorganic film on the wiring;~~

forming a ~~first~~ leveling film ~~containing a siloxane structure~~ formed by a spin coating method on the ~~second inorganic~~ passivation film; and

~~forming a second leveling film containing a siloxane structure on the first leveling film;~~

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~; and~~

~~forming an EL layer over the pixel electrode,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

32. (previously presented) The method according to claim 31, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

33. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming ~~a gate~~ an interlayer insulating film ~~on~~ over the semiconductor film;

forming a ~~gate~~ wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the ~~gate~~ interlayer insulating film;

forming a ~~first leveling~~ passivation film ~~containing a siloxane structure on the second inorganic film~~ deposited on the wiring;

forming a ~~second~~ leveling film ~~containing a siloxane structure~~ formed by a spin coating method on the ~~first leveling~~ passivation film; and

forming a pixel electrode ~~on~~ over the ~~second~~ leveling film~~;~~

~~forming an EL layer over the pixel electrode; and~~

~~enclosing the EL layer by sealing materials with a space between the EL layer and the sealing materials filled by a filler,~~

~~wherein the thickness of the first leveling film is thinner than that of the second leveling film~~.

34. (Previously Presented) The method according to claim 33, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

35. (New) The method according to claim 1, wherein the wiring is formed by a sputtering method.

36. (New) The method according to claim 1, wherein the wiring comprises aluminum.

37. (New) The method according to claim 1, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

38. (New) The method according to claim 1, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

39. (New) The method according to claim 1, wherein the passivation film has a thickness of 50 to 500nm.

40. (New) The method according to claim 1, wherein the passivation film has a thickness of 200 to 300nm.

41. (New) The method according to claim 1, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

42. (New) The method according to claim 1, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

43. (New) The method according to claim 1, wherein the pixel electrode is made of a conductive oxide film.

44. (New) The method according to claim 2, wherein the wiring is formed by a sputtering method.

45. (New) The method according to claim 2, wherein the wiring comprises aluminum.

46. (New) The method according to claim 2, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

47. (New) The method according to claim 2, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

48. (New) The method according to claim 2, wherein the passivation film has a thickness of 50 to 500nm.

49. (New) The method according to claim 2, wherein the passivation film has a thickness of 200 to 300nm.

50. (New) The method according to claim 2, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

51. (New) The method according to claim 2, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

52. (New) The method according to claim 2, wherein the pixel electrode is made of a conductive oxide film.

53. (New) The method according to claim 3, wherein the wiring is formed by a sputtering method.

54. (New) The method according to claim 3, wherein the wiring comprises aluminum.

55. (New) The method according to claim 3, wherein the wiring is a three-layered laminate

film containing a first tantalum film, an aluminum film and a second tantalum film.

56. (New) The method according to claim 3, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

57. (New) The method according to claim 3, wherein the passivation film has a thickness of 50 to 500nm.

58. (New) The method according to claim 3, wherein the passivation film has a thickness of 200 to 300nm.

59. (New) The method according to claim 3, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

60. (New) The method according to claim 3, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

61. (New) The method according to claim 3, wherein the pixel electrode is made of a conductive oxide film.

62. (New) The method according to claim 4, wherein the wiring is formed by a sputtering method.

63. (New) The method according to claim 4, wherein the wiring comprises aluminum.

64. (New) The method according to claim 4, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

65. (New) The method according to claim 4, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

66. (New) The method according to claim 4, wherein the insulating film has a thickness of 50 to 500nm.

67. (New) The method according to claim 4, wherein the insulating film has a thickness of 200 to 300nm.

68. (New) The method according to claim 4, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

69. (New) The method according to claim 4, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

70. (New) The method according to claim 4, wherein the pixel electrode is made of a conductive oxide film.

71. (New) The method according to claim 5, wherein the wiring is formed by a sputtering method.

72. (New) The method according to claim 5, wherein the wiring comprises aluminum.

73. (New) The method according to claim 5, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

74. (New) The method according to claim 5, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

75. (New) The method according to claim 5, wherein the insulating film has a thickness of 50 to 500nm.

76. (New) The method according to claim 5, wherein the insulating film has a thickness of 200 to 300nm.

77. (New) The method according to claim 5, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

78. (New) The method according to claim 5, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

79. (New) The method according to claim 5, wherein the pixel electrode is made of a conductive oxide film.

80. (New) The method according to claim 6, wherein the wiring is formed by a sputtering method.

81. (New) The method according to claim 6, wherein the wiring comprises aluminum.

82. (New) The method according to claim 6, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

83. (New) The method according to claim 6, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

84. (New) The method according to claim 6, wherein the insulating film has a thickness of 50 to 500nm.

85. (New) The method according to claim 6, wherein the insulating film has a thickness of 200 to 300nm.

86. (New) The method according to claim 6, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

87. (New) The method according to claim 6, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

88. (New) The method according to claim 6, wherein the pixel electrode is made of a

conductive oxide film.

89. (New) The method according to claim 7, wherein the wiring is formed by a sputtering method.

90. (New) The method according to claim 7, wherein the wiring comprises aluminum.

91. (New) The method according to claim 7, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

92. (New) The method according to claim 7, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

93. (New) The method according to claim 7, wherein the insulating film has a thickness of 50 to 500nm.

94. (New) The method according to claim 7, wherein the insulating film has a thickness of 200 to 300nm.

95. (New) The method according to claim 7, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

96. (New) The method according to claim 7, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

97. (New) The method according to claim 7, wherein the second hole is formed by a dry etching method.

98. (New) The method according to claim 7, wherein the pixel electrode is made of a conductive oxide film.

99. (New) The method according to claim 8, wherein the wiring is formed by a sputtering method.

100. (New) The method according to claim 8, wherein the wiring comprises aluminum.

101. (New) The method according to claim 8, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

102. (New) The method according to claim 8, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

103. (New) The method according to claim 8, wherein the insulating film has a thickness of 50 to 500nm.

104. (New) The method according to claim 8, wherein the insulating film has a thickness of 200 to 300nm.

105. (New) The method according to claim 8, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

106. (New) The method according to claim 8, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

107. (New) The method according to claim 8, wherein the second hole is formed by a dry etching method.

108. (New) The method according to claim 8, wherein the pixel electrode is made of a conductive oxide film.

109. (New) The method according to claim 9, wherein the wiring is formed by a sputtering method.

110. (New) The method according to claim 9, wherein the wiring comprises aluminum.

111. (New) The method according to claim 9, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

112. (New) The method according to claim 9, wherein the first insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

113. (New) The method according to claim 9, wherein the first insulating film has a

thickness of 50 to 500nm.

114. (New) The method according to claim 9, wherein the first insulating film has a thickness of 200 to 300nm.

115. (New) The method according to claim 9, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

116. (New) The method according to claim 9, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

117. (New) The method according to claim 9, wherein the second hole is formed by a dry etching method.

118. (New) The method according to claim 9, wherein the pixel electrode is made of a conductive oxide film.

119. (New) The method according to claim 10, wherein the wiring is formed by a sputtering method.

120. (New) The method according to claim 10, wherein the wiring comprises aluminum.

121. (New) The method according to claim 10, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

122. (New) The method according to claim 10, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

123. (New) The method according to claim 10, wherein the passivation film has a thickness of 50 to 500nm.

124. (New) The method according to claim 10, wherein the passivation film has a thickness of 200 to 300nm.

125. (New) The method according to claim 10, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

126. (New) The method according to claim 10, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

127. (New) The method according to claim 10, wherein the leveling film comprises an inorganic spin on glass material.

128. (New) The method according to claim 10, wherein the pixel electrode is made of a conductive oxide film.

129. (New) The method according to claim 31, wherein the wiring is formed by a sputtering method.

130. (New) The method according to claim 31, wherein the wiring comprises aluminum.

131. (New) The method according to claim 31, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

132. (New) The method according to claim 31, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

133. (New) The method according to claim 31, wherein the passivation film has a thickness of 50 to 500nm.

134. (New) The method according to claim 31, wherein the passivation film has a thickness of 200 to 300nm.

135. (New) The method according to claim 31, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

136. (New) The method according to claim 31, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

137. (New) The method according to claim 31, wherein the leveling film comprises an inorganic spin on glass material.

138. (New) The method according to claim 31, wherein the pixel electrode is made of a conductive oxide film.

139. (New) The method according to claim 33, wherein the wiring is formed by a sputtering method.

140. (New) The method according to claim 33, wherein the wiring comprises aluminum.

141. (New) The method according to claim 33, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

142. (New) The method according to claim 33, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

143. (New) The method according to claim 33, wherein the passivation film has a thickness of 50 to 500nm.

144. (New) The method according to claim 33, wherein the passivation film has a thickness of 200 to 300nm.

145. (New) The method according to claim 33, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

146. (New) The method according to claim 33, wherein the method further comprises a step

of forming another leveling film formed by a spin coating method on the leveling film.

147. (New) The method according to claim 33, wherein the leveling film comprises an inorganic spin on glass material.

148. (New) The method according to claim 33, wherein the pixel electrode is made of a conductive oxide film.

149. (New) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film directly formed on the wiring;

forming a leveling film formed by a spin coating method on the insulating film; and

forming a pixel electrode over the leveling film.

150. (New) The method according to claim 149, wherein the wiring is formed by a sputtering method.

151. (New) The method according to claim 149, wherein the wiring comprises aluminum.

152. (New) The method according to claim 149, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

153. (New) The method according to claim 149, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

154. (New) The method according to claim 149, wherein the insulating film has a thickness of 50 to 500nm.

155. (New) The method according to claim 149, wherein the insulating film has a thickness of 200 to 300nm.

156. (New) The method according to claim 149, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

157. (New) The method according to claim 149, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

158. (New) The method according to claim 149, wherein the leveling film comprises an inorganic spin on glass material.

159. (New) The method according to claim 149, wherein the pixel electrode is made of a conductive oxide film.

160. (New) The method according to claim 149, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

161. (New) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film covering a surface of the wiring;

forming a leveling film formed by a spin coating method on the insulating film; and

forming a pixel electrode over the leveling film.

162. (New) The method according to claim 161, wherein the wiring is formed by a sputtering method.

163. (New) The method according to claim 161, wherein the wiring comprises aluminum.

164. (New) The method according to claim 161, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

165. (New) The method according to claim 161, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

166. (New) The method according to claim 161, wherein the insulating film has a thickness of 50 to 500nm.

167. (New) The method according to claim 161, wherein the insulating film has a thickness of 200 to 300nm.

168. (New) The method according to claim 161, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

169. (New) The method according to claim 161, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

170. (New) The method according to claim 161, wherein the leveling film comprises an inorganic spin on glass material.

171. (New) The method according to claim 161, wherein the pixel electrode is made of a conductive oxide film.

172. (New) The method according to claim 161, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

173. (New) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film deposited on the wiring;

forming a leveling film formed by a spin coating method on the insulating film; and

forming a pixel electrode over the leveling film.

174. (New) The method according to claim 173, wherein the wiring is formed by a sputtering method.

175. (New) The method according to claim 173, wherein the wiring comprises aluminum.

176. (New) The method according to claim 173, wherein the wiring is a three-layered laminate film containing a first tantalum film, an aluminum film and a second tantalum film.

177. (New) The method according to claim 173, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

178. (New) The method according to claim 173, wherein the insulating film has a thickness of 50 to 500nm.

179. (New) The method according to claim 173, wherein the insulating film has a thickness of 200 to 300nm.

180. (New) The method according to claim 173, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

181. (New) The method according to claim 173, wherein the method further comprises a

step of forming another leveling film formed by a spin coating method on the leveling film.

182. (New) The method according to claim 173, wherein the leveling film comprises an inorganic spin on glass material.

183. (New) The method according to claim 173, wherein the pixel electrode is made of a conductive oxide film.

184. (New) The method according to claim 173, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.